



No.676D

2SB808/2SD1012
 PNP/NPN Epitaxial Planar Silicon Transistors
 Low-Voltage Large-Current
 Amp Applications

(): 2SB808

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

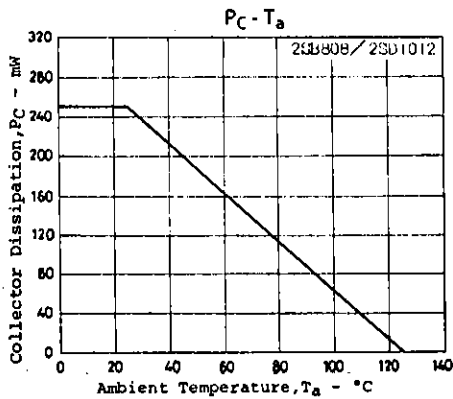
			unit
Collector to Base Voltage	V_{CBO}	(-) 20	V
Collector to Emitter Voltage	V_{CEO}	(-) 15	V
Emitter to Base Voltage	V_{EBO}	(-) 5	V
Collector Current	I_C	(-) 0.7	A
Collector Current(Pulse)	I_{CP}	(-) 1.5	A
Collector Dissipation	P_C	250	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

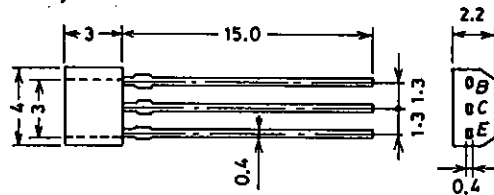
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)15\text{V}, I_E=0$		(-) 1.0		μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4\text{V}, I_C=0$		(-) 1.0		μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=(-)2\text{V}, I_C=(-)50\text{mA}$	160*		960*	
	$h_{FE(2)}$	$V_{CE}=(-)2\text{V}, I_C=(-)500\text{mA}$	80			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10\text{V}, I_C=(-)50\text{mA}$		250		MHz
Common Base Output Capacitance	C_{ob}	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$		(13)		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)1}$	$I_C=(-)5\text{mA}, I_B=(-)0.5\text{mA}$	(-1.5)	(-3.5)		mV
	$V_{CE(sat)2}$	$I_C=(-)100\text{mA}, I_B=(-)10\text{mA}$	(-6.0)	(-12.0)		mV
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)100\text{mA}, I_B=(-)10\text{mA}$	(-) 0.8	(-) 1.2		V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-) 20			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-) 15			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-) 5			V

* The 2SB808/2SD1012 are classified by 50mA h_{FE} as follows :

2SB808	160	F	320	280	G	560	
2SD1012	160	F	320	280	G	560	480 H 960

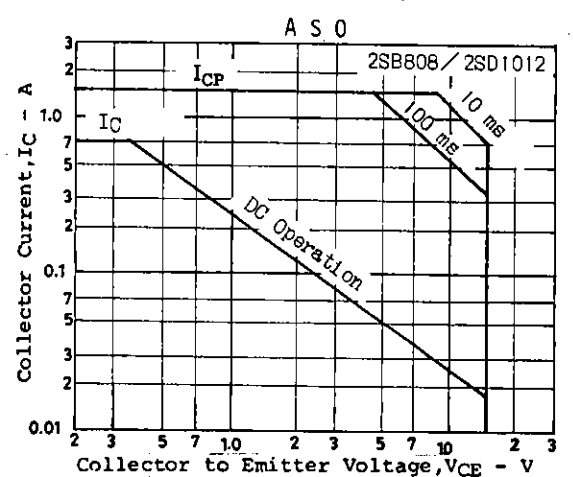
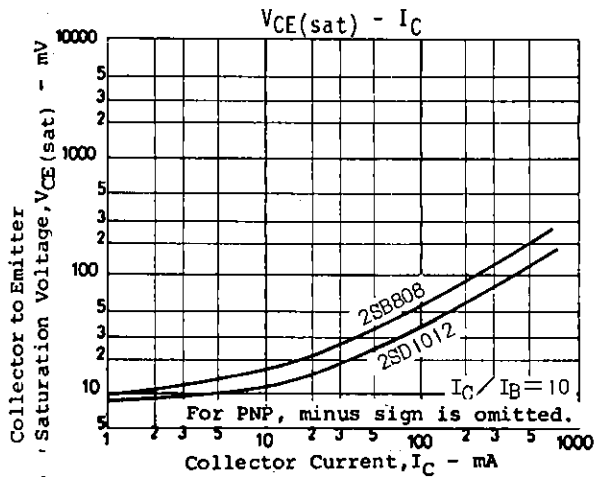
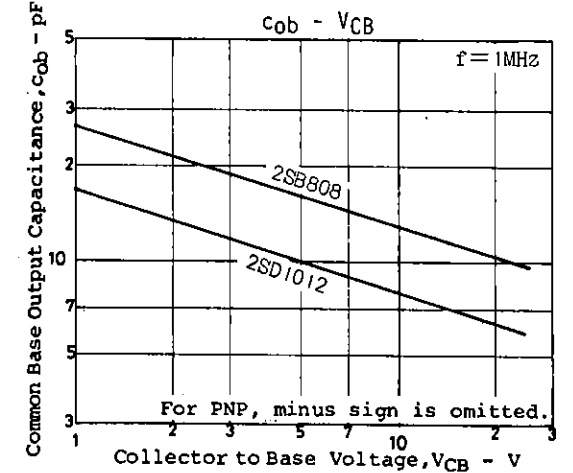
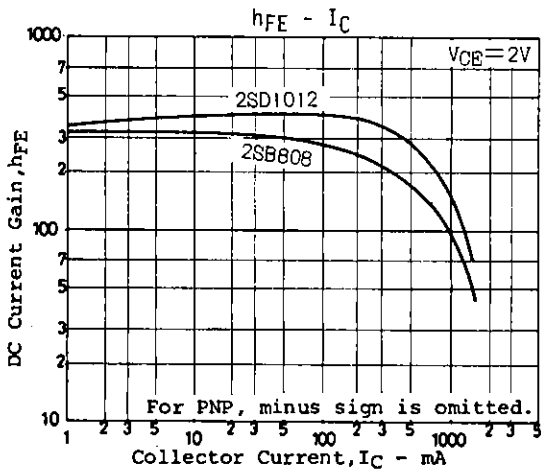
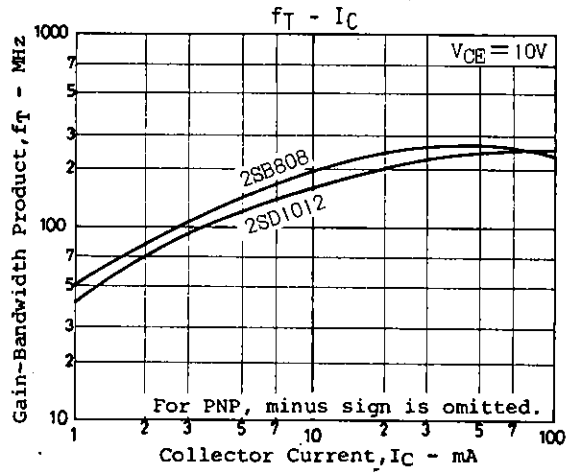
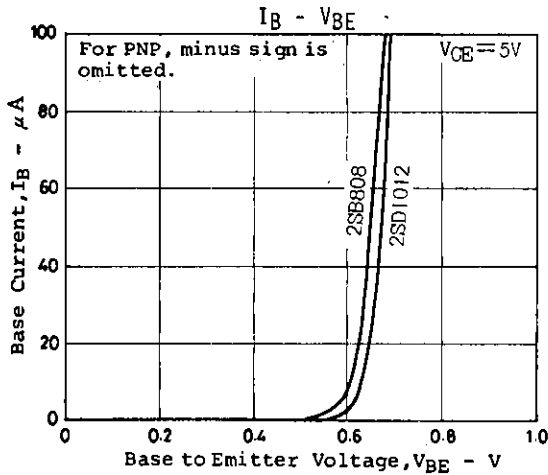
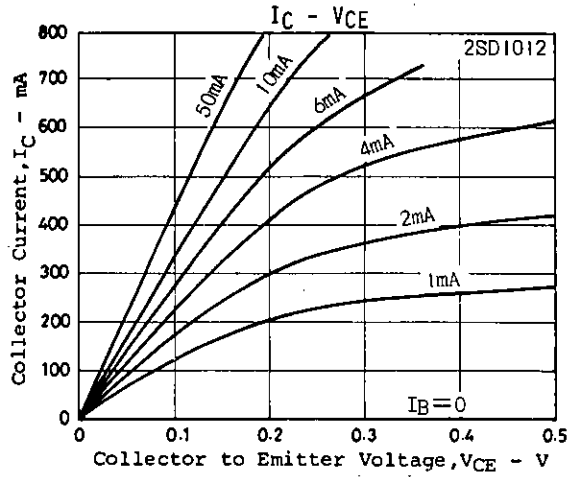
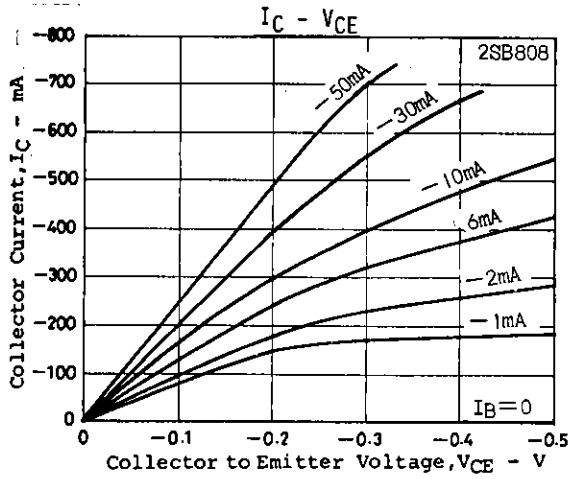


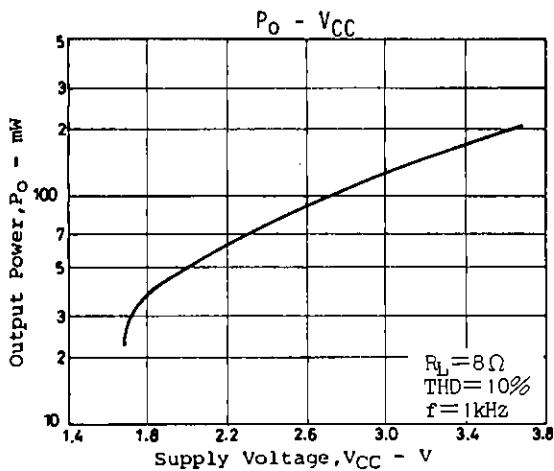
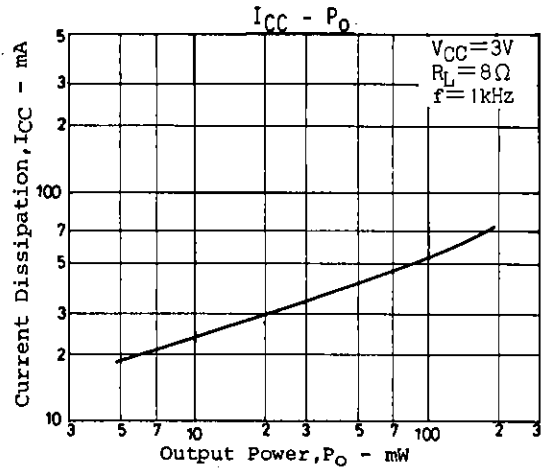
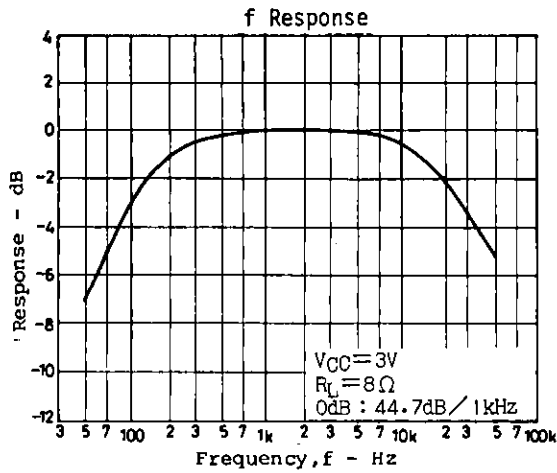
Package Dimensions 2033
 (unit: mm)



B: Base
 C: Collector
 E: Emitter

SANYO: SPA





■ No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.

■ Anyone purchasing any products described or contained herein for an above-mentioned use shall:

- ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use;
- ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.

■ Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.